

Vorläufige Daten
preliminary data

IGBT-Wechselrichter / IGBT-inverter

Höchstzulässige Werte / maximum rated values

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	1200 1600	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_P = 1\text{ ms}$, $T_C = 80^{\circ}\text{C}$	I_{CRM}	2400	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$	P_{tot}	5,95	kW
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / characteristic values

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 1200\text{ A}$, $V_{GE} = 15\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$ $I_C = 1200\text{ A}$, $V_{GE} = 15\text{ V}$, $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{ sat}}$		2,00 2,40	2,45	V V
Gate-Schwellenspannung gate threshold voltage	$I_C = 48,0\text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25^{\circ}\text{C}$	V_{GEth}	5,2	5,8	6,4	V
Gateladung gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$	Q_G		14,0		μC
Interner Gatewiderstand internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}		1,6		Ω
Eingangskapazität input capacitance	$f = 1\text{ MHz}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{ies}		110		nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{ MHz}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{res}		3,50		nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1700\text{ V}$, $V_{GE} = 0\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{CES}			5,0	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{GES}			400	nA
Einschaltverzögerungszeit (ind. Last) turn-on delay time (inductive load)	$I_C = 1200\text{ A}$, $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1,2\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1,2\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ on}}$		0,50 0,54		μs μs
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 1200\text{ A}$, $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1,2\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1,2\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	t_r		0,15 0,16		μs μs
Abschaltverzögerungszeit (ind. Last) turn-off delay time (inductive load)	$I_C = 1200\text{ A}$, $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1,5\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1,5\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ off}}$		1,20 1,40		μs μs
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 1200\text{ A}$, $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1,5\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1,5\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	t_f		0,15 0,26		μs μs
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 1200\text{ A}$, $V_{CE} = 900\text{ V}$, $L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1,2\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1,2\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	E_{on}		230 345		mJ mJ
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 1200\text{ A}$, $V_{CE} = 900\text{ V}$, $L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1,5\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1,5\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	E_{off}		320 430		mJ mJ
Kurzschlußverhalten SC data	$t_P \leq 10\ \mu\text{s}$, $V_{GE} \leq 15\text{ V}$ $T_{vj} \leq 125^{\circ}\text{C}$, $V_{CC} = 1000\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	I_{SC}		4600		A
Innerer Wärmewiderstand thermal resistance, junction to case	pro IGBT per IGBT	R_{thJC}			21,0	K/kW
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{Paste} = 1\text{ W/(m}\cdot\text{K)}$ / $\lambda_{grease} = 1\text{ W/(m}\cdot\text{K)}$	R_{thCH}		17,0		K/kW

Technische Information / technical information

IGBT-Module
IGBT-modules

FF1200R17KE3

eupec



Vorläufige Daten preliminary data

Diode-Wechselrichter / diode-inverter

Höchstzulässige Werte / maximum rated values

Periodische Spitzensperrspannung repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1700	V
Dauergleichstrom DC forward current		I_F	1200	A
Periodischer Spitzenstrom repetitive peak forward current	$t_P = 1 \text{ ms}$	I_{FRM}	2400	A
Grenzlastintegral I^2t - value	$V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	190	kA^2s

Charakteristische Werte / characteristic values

			min.	typ.	max.	
Durchlassspannung forward voltage	$I_F = 1200 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $I_F = 1200 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	V_F		1,80 1,90	2,20	V V
Rückstromspitze peak reverse recovery current	$I_F = 1200 \text{ A}, -di_F/dt = 6900 \text{ A}/\mu\text{s}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	I_{RM}		1100 1350		A A
Sperrverzögerungsladung recovered charge	$I_F = 1200 \text{ A}, -di_F/dt = 6900 \text{ A}/\mu\text{s}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	Q_r		290 505		μC μC
Abschaltenergie pro Puls reverse recovery energy	$I_F = 1200 \text{ A}, -di_F/dt = 6900 \text{ A}/\mu\text{s}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	E_{rec}		190 340		mJ mJ
Innerer Wärmewiderstand thermal resistance, junction to case	pro Diode per diode	R_{thJC}			48,0	K/kW
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) \quad / \quad \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		39,0		K/kW

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Modul / module

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	3,4	kV
Material Modulgrundplatte material of module baseplate			Cu	
Material für innere Isolation material for internal insulation			Al ₂ O ₃	
Kriechstrecke creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		32,0 32,0	mm
Luftstrecke clearance distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		19,0 19,0	mm
Vergleichszahl der Kriechwegbildung comparative tracking index		CTI	> 400	
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R _{thCH}	min. 6,00	typ. max. K/kW
Modulinduktivität stray inductance module		L _{sCE}	20	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	T _C = 25°C, pro Zweig / per arm	R _{CC'+EE'}	0,37	mΩ
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T _{vj max}		150 °C
Temperatur im Schaltbetrieb temperature under switching conditions		T _{vj op}	-40	125 °C
Lagertemperatur storage temperature		T _{stg}	-40	125 °C
Anzugsdrehmoment f. mech. Befestigung mounting torque	Schraube / screw M6	M	4,25	- 5,75 Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	Schraube / screw M4 Schraube / screw M8	M	1,8 8,0	- 2,1 10 Nm
Gewicht weight		G	1500	g

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen technischen Erläuterungen.

This technical information specifies semiconductor devices but guarantees no characteristics. It is valid with the appropriate technical explanations.

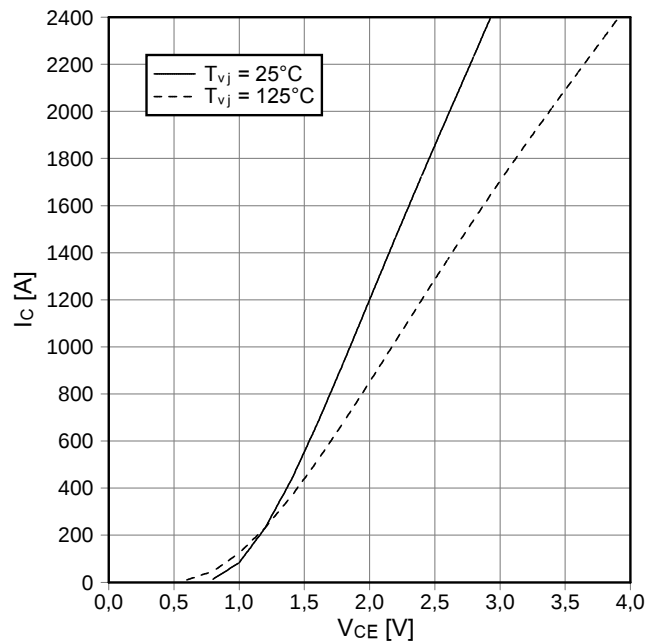
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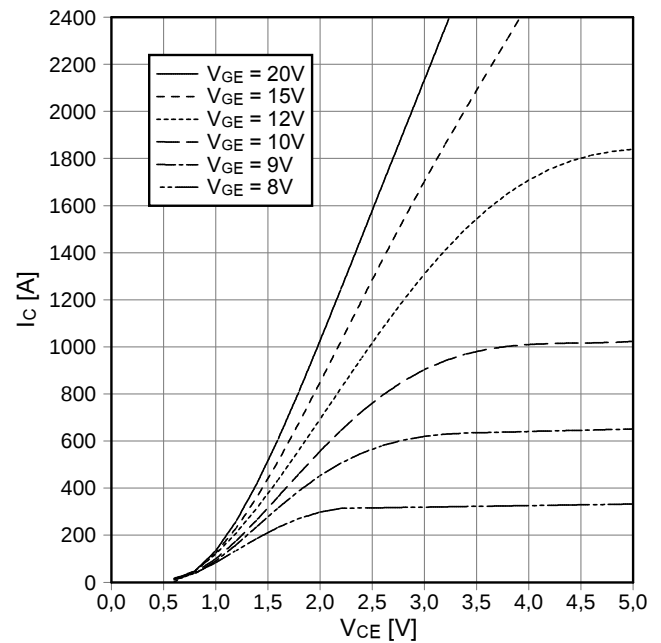
Ausgangskennlinie IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15 \text{ V}$



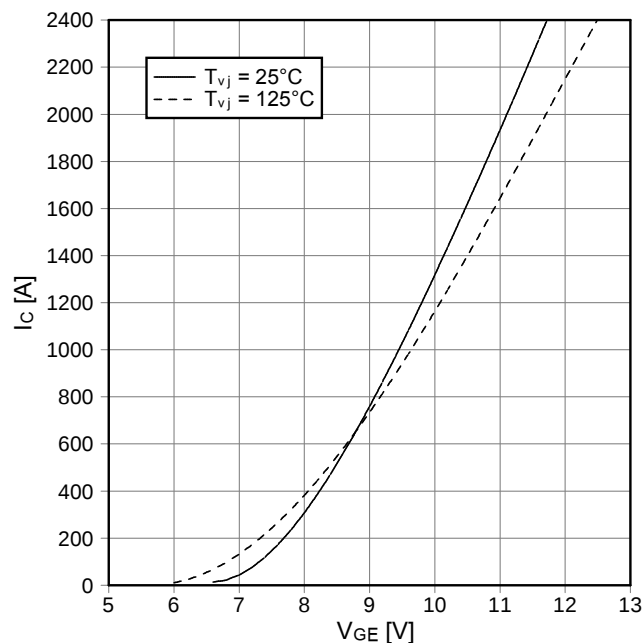
Ausgangskennlinienfeld IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



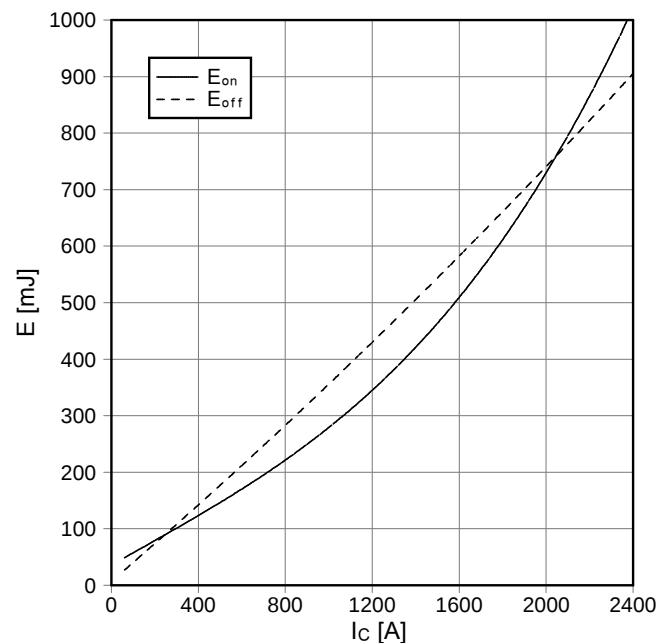
Übertragungscharakteristik IGBT-Wechselr. (typisch)
transfer characteristic IGBT-inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20 \text{ V}$



Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-inverter (typical)

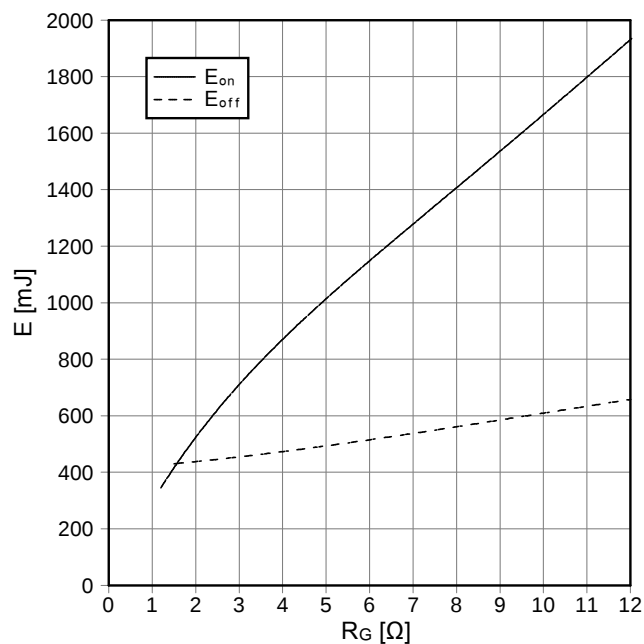
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Gon} = 1,2 \Omega$, $R_{Goff} = 1,5 \Omega$, $V_{CE} = 900 \text{ V}$,
 $T_{vj} = 125^\circ\text{C}$



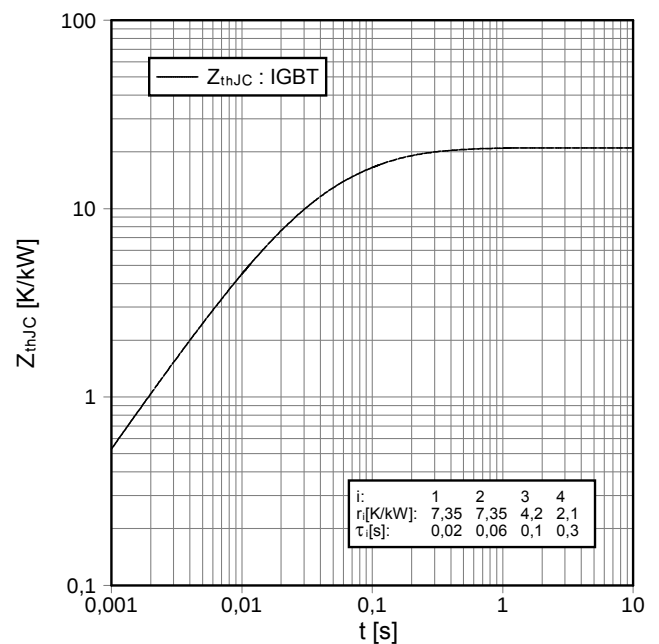


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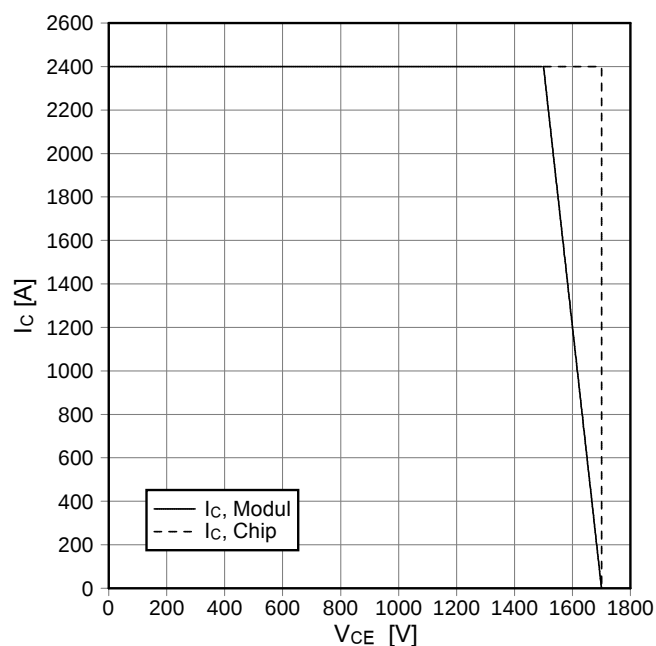
Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-Inverter (typical)
 $E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}$, $I_C = 1200 \text{ A}$, $V_{CE} = 900 \text{ V}$, $T_{vj} = 125^\circ\text{C}$



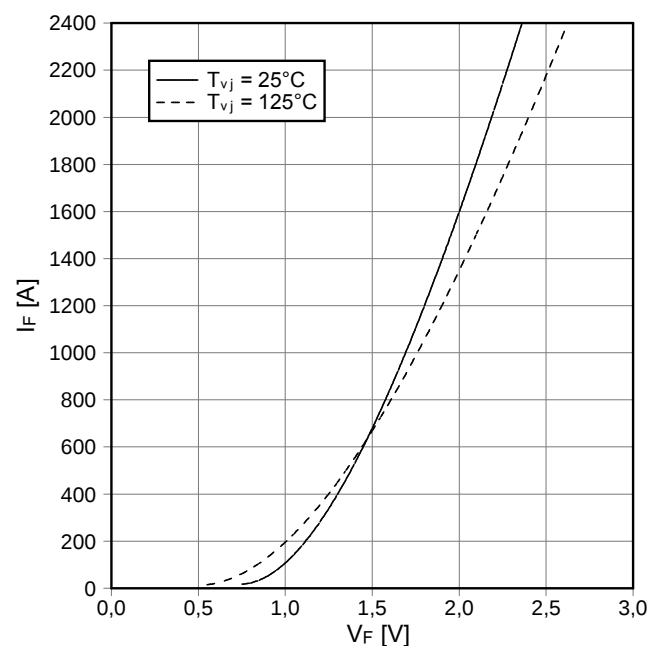
Transienter Wärmewiderstand IGBT-Wechselr.
transient thermal impedance IGBT-inverter
 $Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)
reverse bias safe operating area IGBT-inv. (RBSOA)
 $I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 1,5 \Omega$, $T_{vj} = 125^\circ\text{C}$



Durchlaßkennlinie der Diode-Wechselr. (typisch)
forward characteristic of diode-inverter (typical)
 $I_F = f(V_F)$

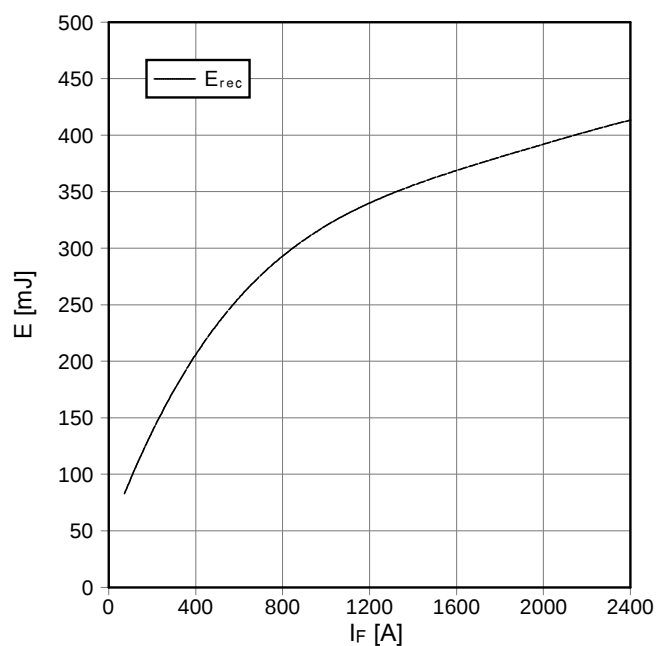


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Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)

$$E_{rec} = f(I_F)$$

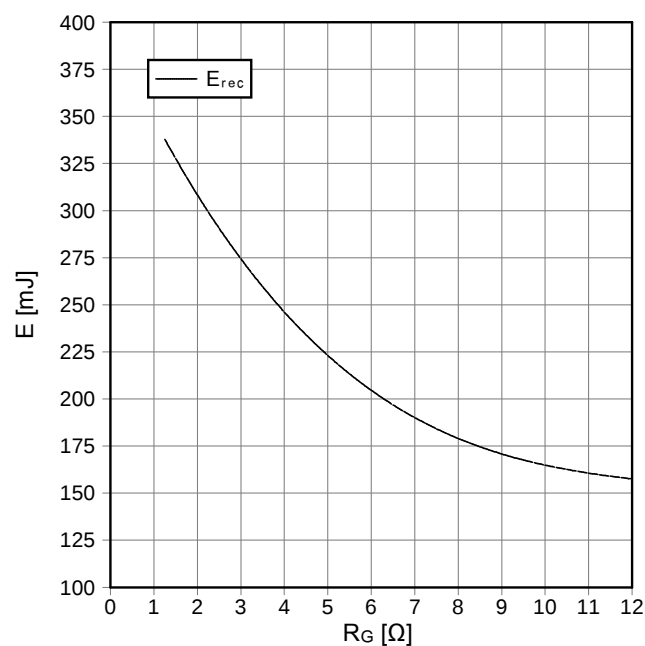
$R_{Gon} = 1,2 \Omega$, $V_{CE} = 900 \text{ V}$, $T_{vj} = 125^\circ\text{C}$



Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)

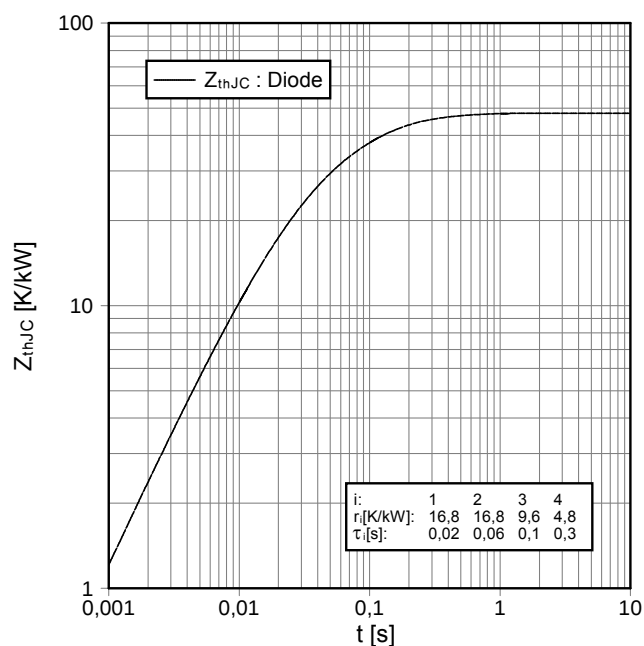
$$E_{rec} = f(R_G)$$

$I_F = 1200 \text{ A}$, $V_{CE} = 900 \text{ V}$, $T_{vj} = 125^\circ\text{C}$



Transienter Wärmewiderstand Diode-Wechselr.
transient thermal impedance diode-inverter

$$Z_{thJC} = f(t)$$



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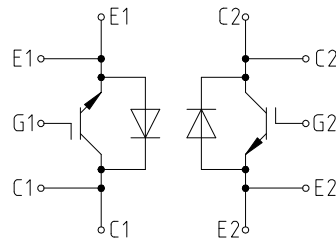
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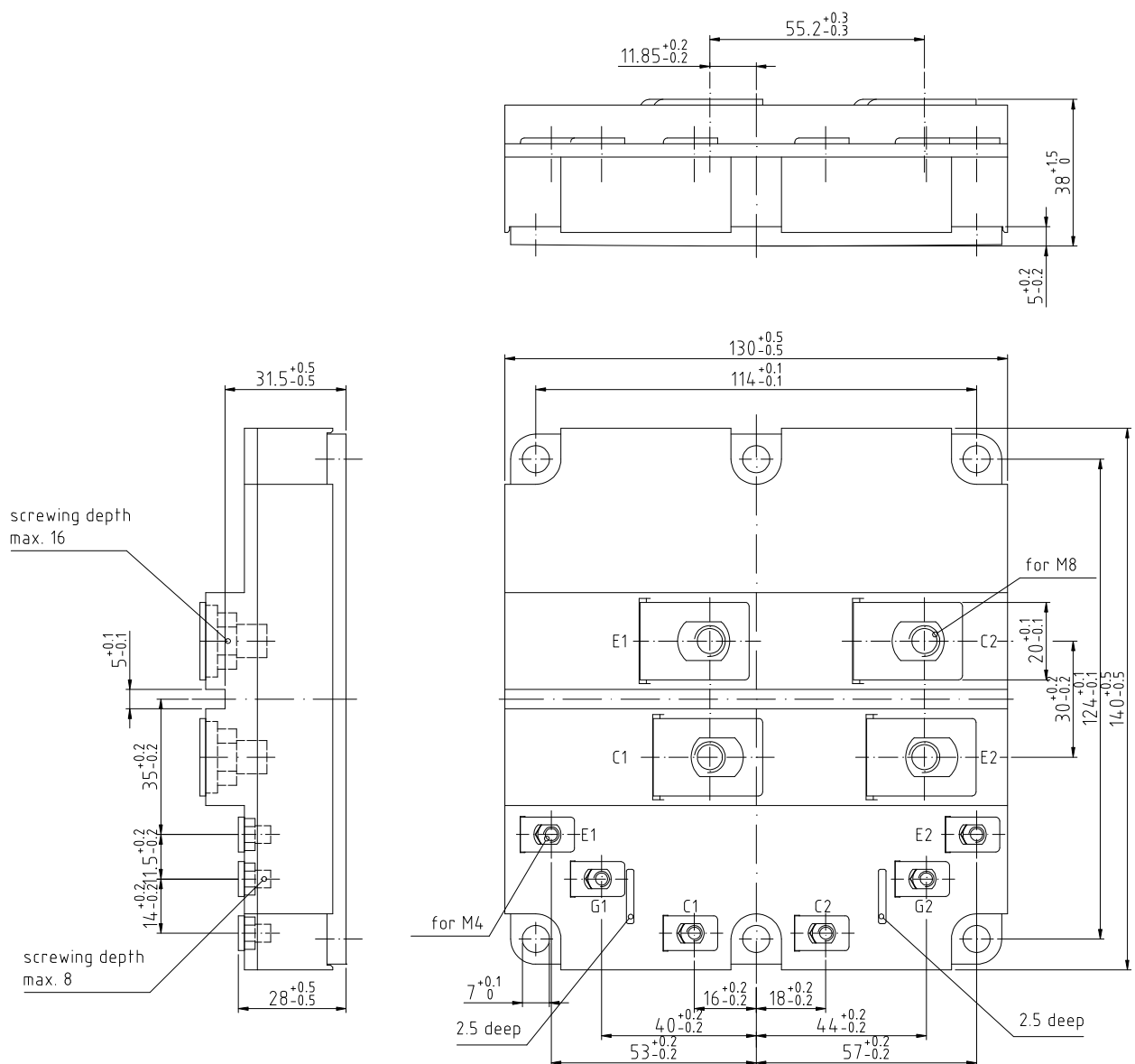


Vorläufige Daten
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Schaltplan / circuit diagram



Gehäuseabmessungen / package outlines



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